

# **Maximum Ratings** $(@T_A = +25^{\circ}C, \text{ unless otherwise specified.})$

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			$V_{DSS}$	60	V
Gate-Source Voltage			$V_{GSS}$	±40	V
Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V	Steady State	$T_A = +25^{\circ}C$ $T_A = +85^{\circ}C$	I <sub>D</sub>	210 150	mA
Maximum Body Diode Forward Current (Note 6)			Is	500	mA
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I <sub>DM</sub>	800	mA

## Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		$P_{D}$	340	mW
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	376	°C/W
Total Power Dissipation (Note 6)		P <sub>D</sub>	570	mW
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	224	°C/W
Operating and Storage Temperature Range		T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C

### **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

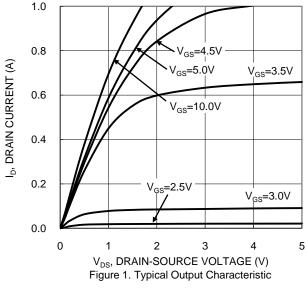
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	60	_	_	V	$V_{GS} = 0V, I_D = 10\mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	1.0	μΑ	$V_{DS} = 60V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	0.8	_	2.5	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance		_	3.2	7.5	Ω	$V_{GS} = 5.0V, I_D = 0.05A$	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>		1.5	5.0		$V_{GS} = 10V, I_D = 0.5A$	
Diode Forward Voltage	V <sub>SD</sub>	_	0.78	1.5	V	$V_{GS} = 0V, I_{S} = 115mA$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C <sub>iss</sub>		22	_	pF	V 05V V 0V	
Output Capacitance	Coss		4.1	_	pF	$V_{DS} = 25V, V_{GS} = 0V,$ f = 1.0MHz	
Reverse Transfer Capacitance	C <sub>rss</sub>	_	2.5	_	pF		
Gate Resistance	Rg	_	120	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Qg	_	361	_			
Total Gate Charge (V <sub>GS</sub> = 10V)	Qg	_	821	_	рС	$V_{DS} = 10V, I_D = 250mA$	
Gate-Source Charge	$Q_{gs}$	_	162	_	] PC		
Gate-Drain Charge	$Q_{qd}$	_	116	_			
Turn-On Delay Time	t <sub>D(ON)</sub>	_	2.8	_		$V_{DD} = 30V, I_D = 0.2A,$ $R_L = 150\Omega, V_{GEN} = 10V,$ $R_{GEN} = 25\Omega$	
Turn-On Rise Time	t <sub>R</sub>	_	3.0		]		
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	7.6		ns		
Turn-Off Fall Time	t <sub>F</sub>	_	5.6	_			

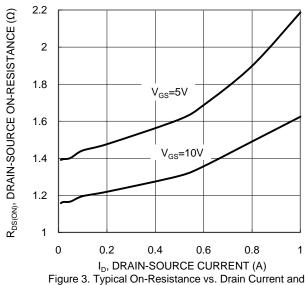
5. Device mounted on FR-4 PCB, with minimum recommended pad layout.

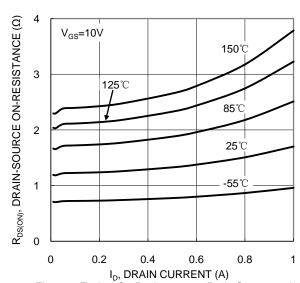
- 6. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
  7. Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to product testing.





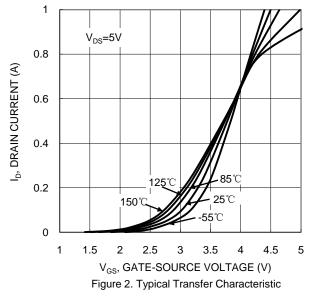






Gate Voltage

Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature



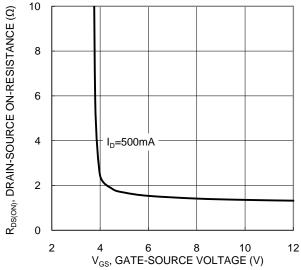


Figure 4. Typical Transfer Characteristic

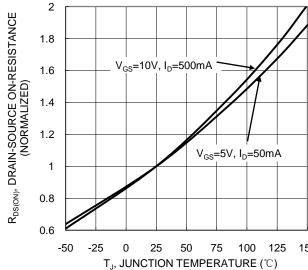


Figure 6. On-Resistance Variation with Junction
Temperature





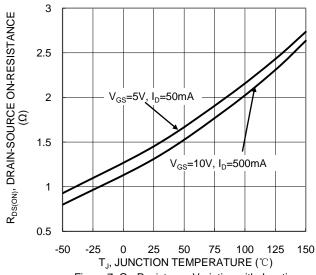
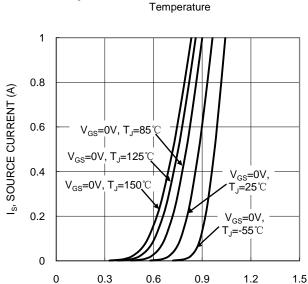


Figure 7. On-Resistance Variation with Junction Temperature



V<sub>SD</sub>, SOURCE-DRAIN VOLTAGE (V) Figure 9. Diode Forward Voltage vs. Current

10 8 6  $V_{GS}(V)$  $V_{DS}$ =10V,  $I_{D}$ =250mA 4 2 0 0 0.2 0.6 8.0 1 0.4  $\mathbf{Q_g} \, (\mathbf{nC})$ Figure 11. Gate Charge

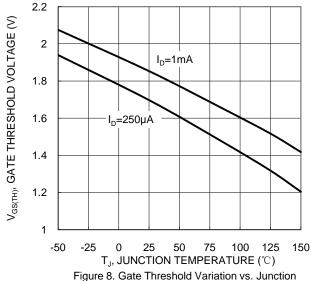
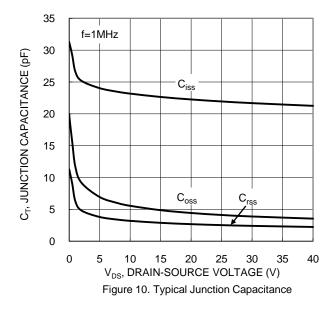
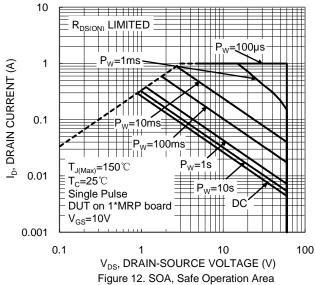


Figure 8. Gate Threshold Variation vs. Junction Temperature







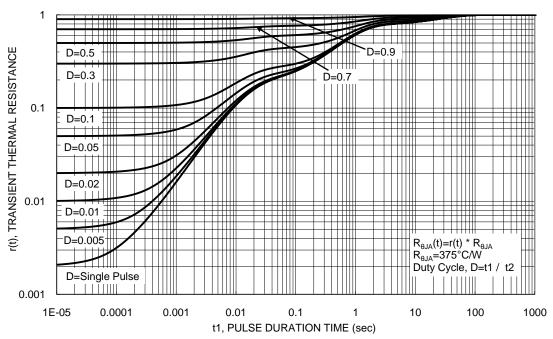


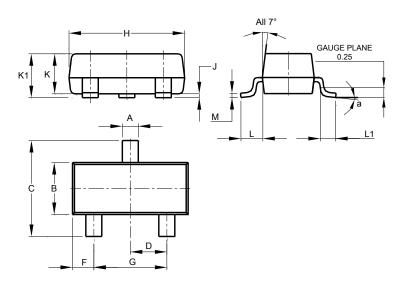
Figure 13. Transient Thermal Resistance



## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### SOT23

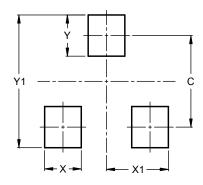


SOT23						
Dim	Min	Max	Тур			
Α	0.37	0.51	0.40			
В	1.20	1.40	1.30			
С	2.30	2.50	2.40			
D	0.89	1.03	0.915			
F	0.45	0.60	0.535			
G	1.78	2.05	1.83			
Н	2.80	3.00	2.90			
J	0.013	0.10	0.05			
K	0.890	1.00	0.975			
K1	0.903	1.10	1.025			
L	0.45	0.61	0.55			
L1	0.25	0.55	0.40			
М	0.085	0.150	0.110			
а	0°	8°				
All Dimensions in mm						

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### SOT23



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Y	0.9
V1	2.0



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